

Title (en)
PASSIVATION OF GAN BASED FETS

Title (de)
PASSIVIERUNG EINES GaN FETS

Title (fr)
PASSIVATION DE TRANSISTORS A EFFET DE CHAMP A BASE DE GAN

Publication
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Application
EP 00957262 A 20000816

Priority
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Abstract (en)
[origin: WO0113436A1] Surface passivation of GaN based FETs, including undoped AlGaIn/GaN HEMTs and MISFETs, and doped GaN MESFETs, reduces or eliminates the surface effects responsible for limiting both the RF current and breakdown voltages of the devices. Passivation is provided through deposition of a layer (32) made of a dielectric, such as silicon nitride, silicon dioxide or polyimide, on a barrier layer (16) between a source (24) and a drain (25) of the FET (10).

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IPC 8 full level
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